



ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748-5089

NTE331 (NPN) & NTE332 (PNP) Silicon Complementary Transistors Audio Power Amp, Switch

Description:

The NTE331 (NPN) and NTE332 (PNP) are silicon epitaxial–base complementary power transistors in a TO–220 plastic package intended for use in power linear and switching applications.

Absolute Maximum Ratings:

Collector–Base Voltage ($I_E = 0$), V_{CBO}	100V
Collector–Emitter Voltage ($I_B = 0$), V_{CEO}	100V
Emitter–Base Voltage ($I_C = 0$), V_{EBO}	5V
Emitter Current, I_E	15A
Collector Current, I_C	15A
Base Current, I_B	5A
Total Power Dissipation ($T_C \leq +25^\circ\text{C}$), P_D	90W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	–65° to +150°C
Thermal Resistance Junction–to–Case, R_{thJC}	1.4°C/W Max

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$I_E = 0, V_{CB} = 100V$	–	–	500	μA
		$I_E = 0, V_{CB} = 100V, T_C = +150^\circ\text{C}$	–	–	5	mA
Collector Cutoff Current	I_{CEO}	$I_B = 0, V_{CE} = 50V$	–	–	1	mA
Emitter Cutoff Current	I_{EBO}	$I_C = 0, V_{EB} = 5V$	–	–	1	mA
Collector–Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_B = 0, I_C = 100\text{mA}, \text{Note 1}$	100	–	–	V
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5A, I_B = 0.5A, \text{Note 1}$	–	–	1	V
		$I_C = 10A, I_B = 2.5A, \text{Note 1}$	–	–	3	V



Electrical Characteristics (Cont'd): ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10\text{A}, I_B = 2.5\text{A}, \text{Note 1}$	–	–	2.5	V
Base–Emitter Voltage	V_{BE}	$I_C = 5\text{A}, V_{CE} = 4\text{V}, \text{Note 1}$	–	–	1.5	V
DC Current Gain	h_{FE}	$I_C = 0.5\text{A}, V_{CE} = 4\text{V}, \text{Note 1}$	40	–	250	
		$I_C = 5\text{A}, V_{CE} = 4\text{V}, \text{Note 1}$	15	–	150	
		$I_C = 10\text{A}, V_{CE} = 4\text{V}, \text{Note 1}$	5	–	–	
Transistion Frequency	f_T	$I_C = 0.5\text{A}, V_{CE} = 4\text{V}$	3	–	–	MHz

Note 1. Pulsed; Pulse Duration = $300\mu\text{s}$, Duty Cycle = 1.5%.

